

**FEATURES** **IEEE802.3af Compatible**

- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 10  $\mu$ A (Max.) @  $V_{DS} = 100V$
- Lower  $R_{DS(ON)}$  : 0.155  $\Omega$  (Typ.)

$BV_{DSS} = 100 V$   
 $R_{DS(on)} = 0.2 \Omega$   
 $I_D = 2.3 A$

**SOT-223**



1. Gate 2. Drain 3. Source

**Absolute Maximum Ratings**

Symbol	Characteristic	Value	Units
$V_{DSS}$	Drain-to-Source Voltage	100	V
$I_D$	Continuous Drain Current ( $T_A=25^\circ C$ )	2.3	A
	Continuous Drain Current ( $T_A=70^\circ C$ )	1.84	
$I_{DM}$	Drain Current-Pulsed <sup>①</sup>	18	A
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulsed Avalanche Energy <sup>②</sup>	123	mJ
$I_{AR}$	Avalanche Current <sup>①</sup>	2.3	A
$E_{AR}$	Repetitive Avalanche Energy <sup>①</sup>	0.24	mJ
dv/dt	Peak Diode Recovery dv/dt <sup>③</sup>	6.5	V/ns
$P_D$	Total Power Dissipation ( $T_A=25^\circ C$ ) *	2.4	W
	Linear Derating Factor *	0.019	
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	- 55 to +150	$^\circ C$
$T_L$	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

**Thermal Resistance**

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient *	--	52	$^\circ C/W$

\* When mounted on the minimum pad size recommended (PCB Mount).

## Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$BV_{DSS}$	Drain-Source Breakdown Voltage	100	--	--	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.12	--	V/ $^\circ\text{C}$	$I_D=250\mu A$ <b>See Fig 7</b>
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS}=5V, I_D=250\mu A$
$I_{GSS}$	Gate-Source Leakage, Forward	--	--	100	nA	$V_{GS}=20V$
	Gate-Source Leakage, Reverse	--	--	-100		$V_{GS}=-20V$
$I_{DSS}$	Drain-to-Source Leakage Current	--	--	1	$\mu A$	$V_{DS}=30V$ ⑥
		--	--	10		$V_{DS}=100V$
		--	--	100		$V_{DS}=80V, T_A=125^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.2	$\Omega$	$V_{GS}=10V, I_D=1.15A$ ④
$g_{fs}$	Forward Transconductance	--	3.12	--	S	$V_{DS}=40V, I_D=1.15A$ ④
$C_{iss}$	Input Capacitance	--	370	480	pF	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$ <b>See Fig 5</b>
$C_{oss}$	Output Capacitance	--	95	110		
$C_{rss}$	Reverse Transfer Capacitance	--	38	45		
$t_{d(on)}$	Turn-On Delay Time	--	14	40	ns	$V_{DD}=50V, I_D=9.2A,$ $R_G=18\Omega$ <b>See Fig 13</b> ④ ⑤
$t_r$	Rise Time	--	14	40		
$t_{d(off)}$	Turn-Off Delay Time	--	36	90		
$t_f$	Fall Time	--	28	70		
$Q_g$	Total Gate Charge	--	16	22	nC	$V_{DS}=80V, V_{GS}=10V,$ $I_D=9.2A$ <b>See Fig 6 &amp; Fig 12</b> ④ ⑤
$Q_{gs}$	Gate-Source Charge	--	2.7	--		
$Q_{gd}$	Gate-Drain("Miller") Charge	--	7.8	--		

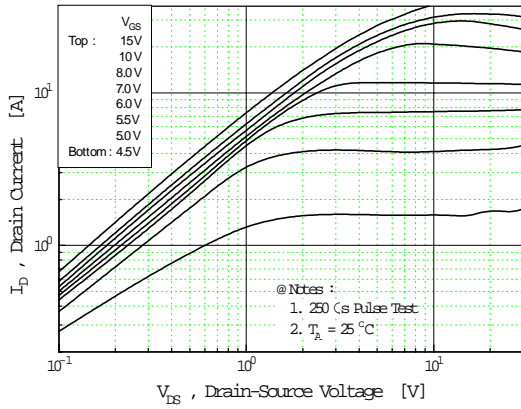
## Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$I_S$	Continuous Source Current	--	--	2.3	A	Integral reverse pn-diode in the MOSFET
$I_{SM}$	Pulsed-Source Current ①	--	--	18		
$V_{SD}$	Diode Forward Voltage ④	--	--	1.5	V	$T_J=25^\circ\text{C}, I_S=2.3A, V_{GS}=0V$
$t_{rr}$	Reverse Recovery Time	--	98	--	ns	$T_J=25^\circ\text{C}, I_F=9.2A$
$Q_{rr}$	Reverse Recovery Charge	--	0.34	--	$\mu C$	$di_F/dt=100A/\mu s$ ④

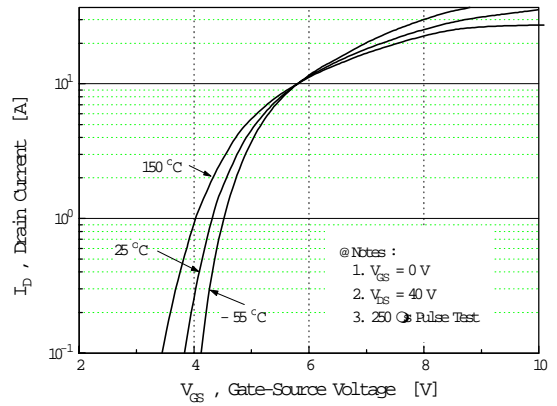
### Notes ;

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ②  $L=35\text{mH}, I_{AS}=2.3A, V_{DD}=25V, R_G=27\Omega,$  Starting  $T_J=25^\circ\text{C}$
- ③  $I_{SD}\leq 9.2A, di/dt\leq 300A/\mu s, V_{DD}\leq BV_{DSS},$  Starting  $T_J=25^\circ\text{C}$
- ④ Pulse Test : Pulse Width =  $250\mu s,$  Duty Cycle  $\leq 2\%$
- ⑤ Essentially Independent of Operating Temperature
- ⑥ Adjusted for Cisco

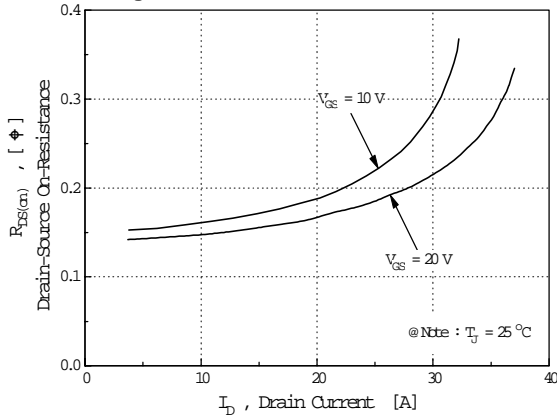
**Fig 1. Output Characteristics**



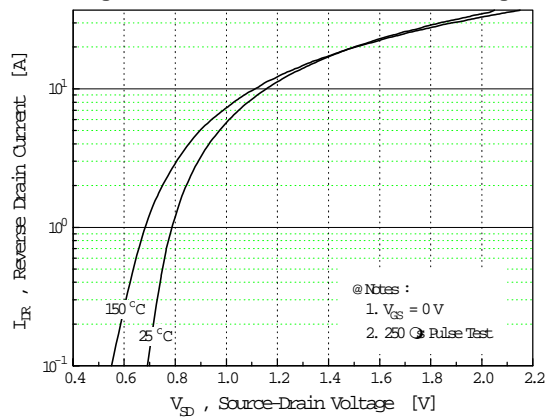
**Fig 2. Transfer Characteristics**



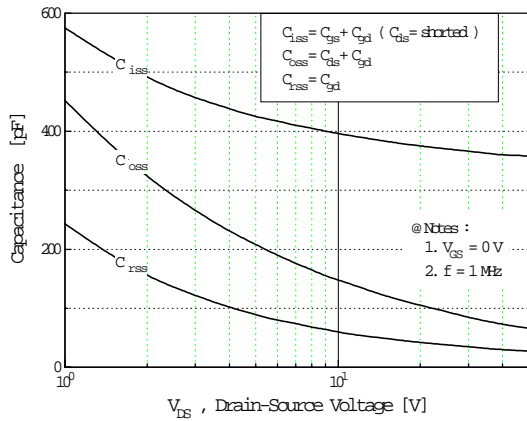
**Fig 3. On-Resistance vs. Drain Current**



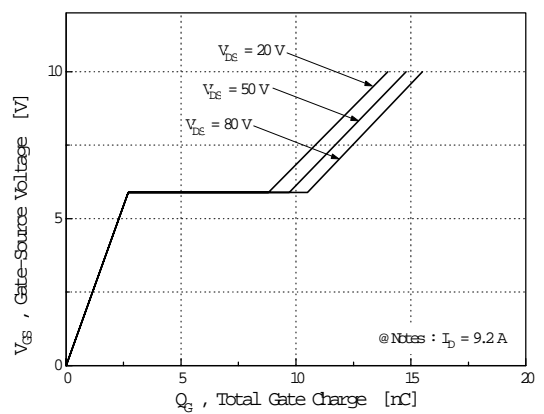
**Fig 4. Source-Drain Diode Forward Voltage**



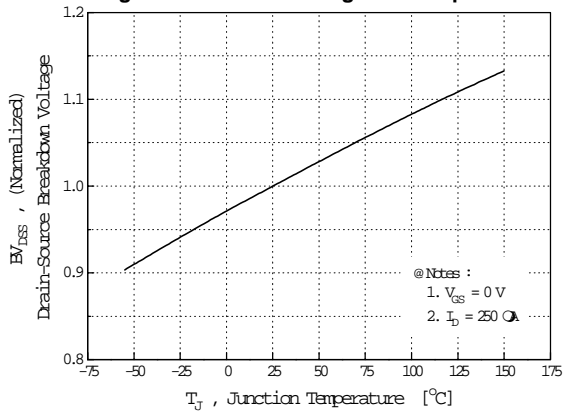
**Fig 5. Capacitance vs. Drain-Source Voltage**



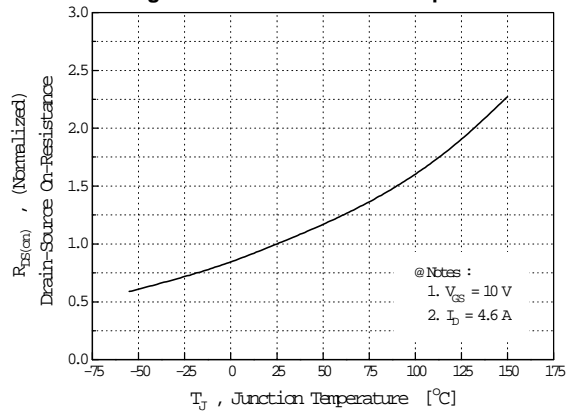
**Fig 6. Gate Charge vs. Gate-Source Voltage**



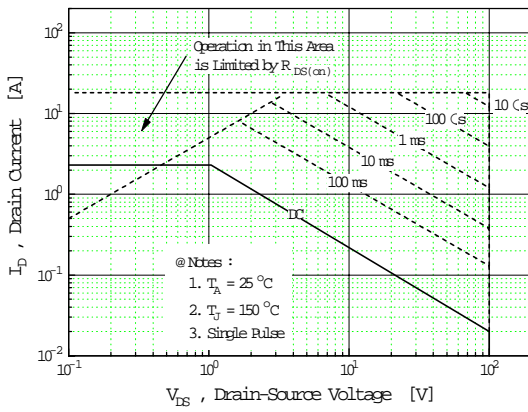
**Fig 7. Breakdown Voltage vs. Temperature**



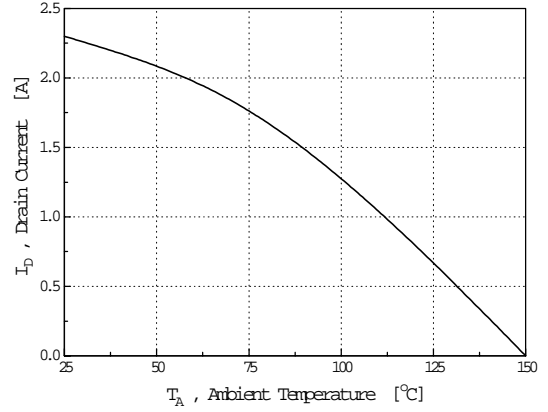
**Fig 8. On-Resistance vs. Temperature**



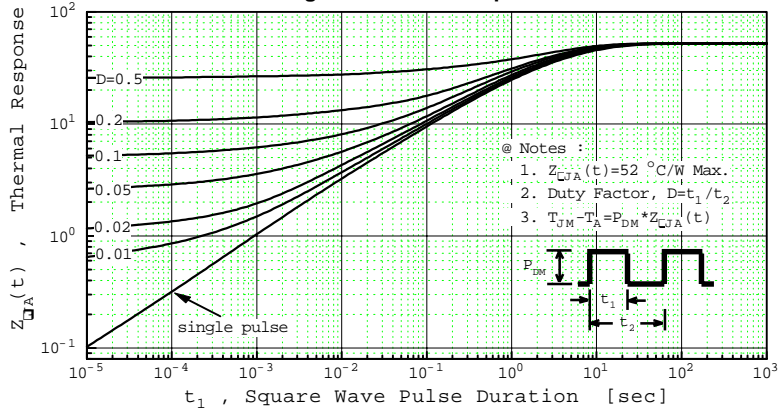
**Fig 9. Max. Safe Operating Area**



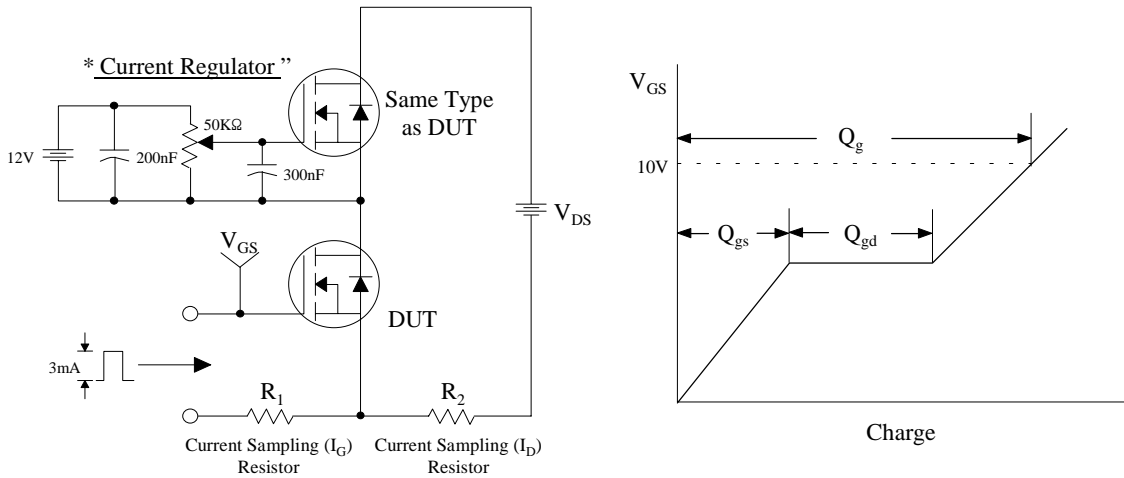
**Fig 10. Max. Drain Current vs. Ambient Temperature**



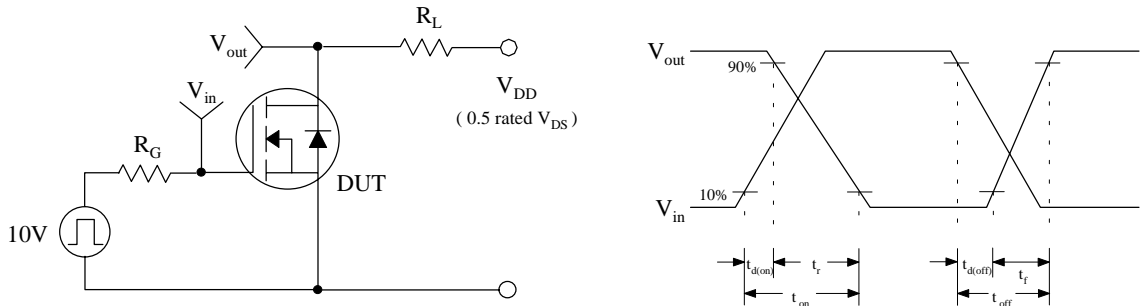
**Fig 11. Thermal Response**



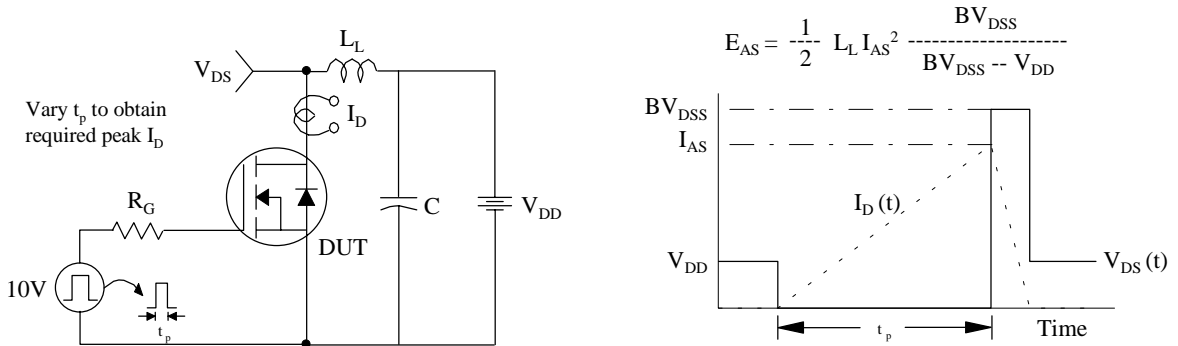
**Fig 12. Gate Charge Test Circuit & Waveform**



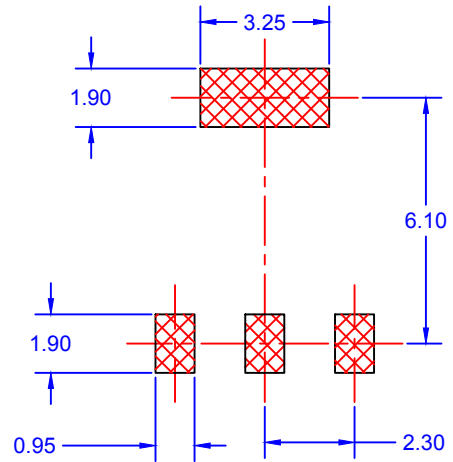
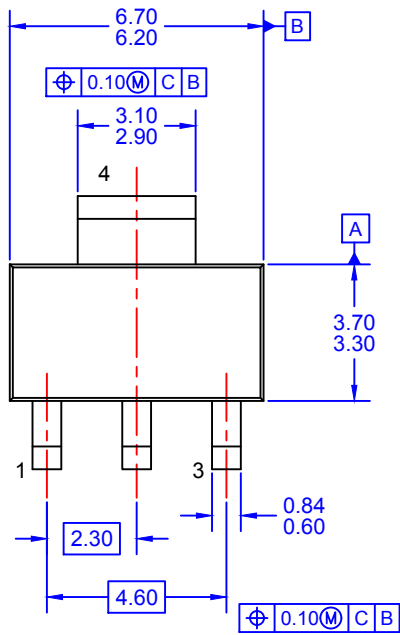
**Fig 13. Resistive Switching Test Circuit & Waveforms**



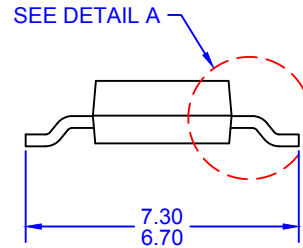
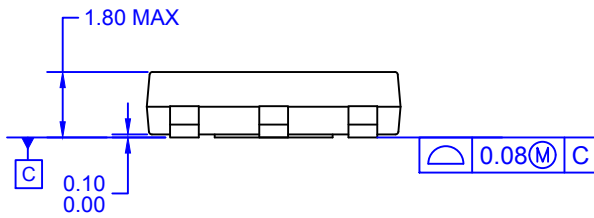
**Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms**



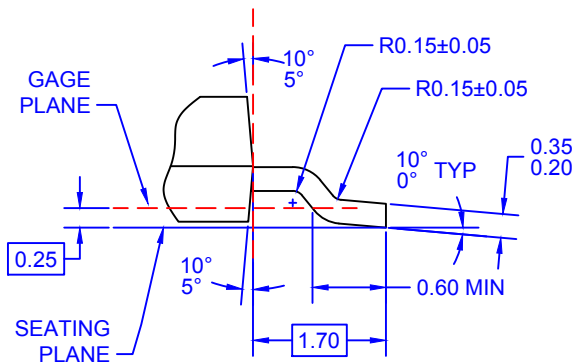




LAND PATTERN RECOMMENDATION



SEE DETAIL A



DETAIL A  
SCALE: 2:1






- NOTES: UNLESS OTHERWISE SPECIFIED  
 A) DRAWING BASED ON JEDEC REGISTRATION TO-261C, VARIATION AA.  
 B) ALL DIMENSIONS ARE IN MILLIMETERS.  
 C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.  
 D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.  
 E) LANDPATTERN NAME: SOT230P700X180-4BN  
 F) DRAWING FILENAME: MKT-MA04AREV3





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